編號:

203, 204, 217

國立成功大學九十九學年度碩士班招生考試試題

共 之 頁,第/頁

系所組別: 微電子工程研究所,電機系甲乙丁戊組,電通所丙丁組

考試科目: 電子學

考試日期:0307・節次:1

※ 考生請注意:本試題 ☑可 □不可 使用計算機

- 1. Determine the current I_{D2} and the voltage V_0 in the diode circuit shown in Fig. 1. Assume the turn-on voltage of $V_{\gamma}=0.7V$ for each diode. (10%)
- 2. A Schottky TTL logic circuit is shown in **Fig. 2**. Assume the turn-on voltages of V_{γ} =0.7V and $V_{\gamma}(SD)$ =0.3V are used for all diodes and Shottky diodes, respectively. Also, the turn-on voltage of B-E junction $V_{BE}(on)$ =0.7V and common-emitter current gain of β = 30 are employed for all transistors. (a) Calculate the maximum fan-out for V_{X} = V_{Y} =3.6V. (b) Using the results of part (a), determine the power dissipated in this circuit for V_{X} = V_{Y} =3.6V. (22%)
- 3. Assume the input signal to the circuit in Fig. 3 is $v_l = 75\sin(120\pi t)$ V and the diode has a cut-in voltage (V_r) of 0.7 V.
- (a) Calculate the average value of the output voltage v_0 . (5%)
- (b) If a capacitor (50 μ F) is added in parallel with the load resistor R_L and the ripple voltage is to be
- ≤ 4 V, determine the minimum value of R_L for the case of $V_V = 0$ V and $V_V = 0.7$ V, respectively. (10%)
- 4. Assume the circuit in Fig. 4 is a symmetrical circuit. Derive the ac component of the output voltage v_O for the case of $v_{G1} = v_{G2}$ and $v_{G1} < v_{G2}$, respectively. (10%)
- 5. Plot transfer curve of the circuit in Fig. 5.
- (a) Assume an ideal operational amplifier (op-amp). (4%)
- (b) Assume the op-amp has a finite voltage gain (i.e., $A_{ij} \neq \infty$). (5%)
- 6. A feedback amplifier is shown in the Fig. 6, neglect r_o and body effect of the MOSFET devices. The parameters of M_1 and M_2 : $g_{m1} = g_{m2} = 5$ mA/V.
- (a) Which topology is for this feedback amplifier? (4%)
- (b) Calculate the feedback factor β . (5%)
- (c) Find the voltage gain v_O/v_S , the input resistance R_{in} , and the output resistance R_{out} . (9%)
- 7. Consider the class AB Amplifier as shown in Fig. 7.

The circuit is biased with $V_{CC}=12~V$, and $I_{BIAS}=20~mA$, the load resistance $R_L=8~\Omega$.

The device parameters are: $I_{SD} = 3 \times 10^{-14} A$ for diodes, and $I_{SQ} = 10^{-13} A$ for Q_N and Q_P , $\beta_R = \beta_P = 75$.

The minimum value for diode current is to be no less than 5 mA

- (a) Find the quiescent collector current I_{CQ} for Q_N and Q_P . (8%)
- (b) Calculate the maximum average power delivered to the load. (8%)

編號:

203, 204, 217

國立成功大學九十九學年度碩士班招生考試試題

共之頁,第之頁

系所組別: 微電子工程研究所,電機系甲乙丁戊組,電通所丙丁組

考試科目: 電子學

